

CVFD20065A

Silicon Carbide Schottky Diode

Z-REC[®] RECTIFIER

V_{RRM}	=	650 V
$I_F (T_c=135^\circ\text{C})$	=	26 A
Q_c	=	62 nC

Features

- 650-Volt Schottky Rectifier
- Reduced V_F for Improved Efficiency
- High Humidity Resistance
- Zero Forward and Reverse Recovery Voltage
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

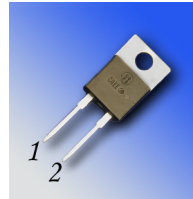
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Power Inverters
- Motor Drives
- EV Chargers
- Power Factor Correction
- Server Power Supplies

Package



TO-220-2



Part Number	Package	Marking
CVFD20065A	TO-220-2	CVFD20065

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{RSM}	Surge Peak Reverse Voltage	650	V		
V_{DC}	DC Peak Blocking Voltage	650	V		
I_F	Continuous Forward Current	57 26 20	A	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=149^\circ\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	91 61.5	A	$T_c=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	206 180	A	$T_c=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
$I_{F,Max}$	Non-Repetitive Peak Forward Current	1400 1100	A	$T_c=25^\circ\text{C}$, $t_p=10$ μs , Pulse $T_c=110^\circ\text{C}$, $t_p=10$ μs , Pulse	
P_{tot}	Power Dissipation	187.5 81	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.35 1.65	1.45 1.80	V	$I_F = 20 \text{ A}$, $T_J = 25^\circ\text{C}$ $I_F = 20 \text{ A}$, $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	8 2	80	μA	$V_R = 650 \text{ V}$, $T_J = 25^\circ\text{C}$ $V_R = 400 \text{ V}$, $T_J = 25^\circ\text{C}$	
		30 5	300	μA	$V_R = 650 \text{ V}$, $T_J = 175^\circ\text{C}$ $V_R = 400 \text{ V}$, $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	62		nC	$V_R = 400 \text{ V}$ $di/dt = 500 \text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	1100		pF	$V_R = 0 \text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1 \text{ MHz}$ $V_R = 200 \text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1 \text{ MHz}$ $V_R = 400 \text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1 \text{ MHz}$	
		113				
		108				

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.8	$^\circ\text{C}/\text{W}$

Typical Performance

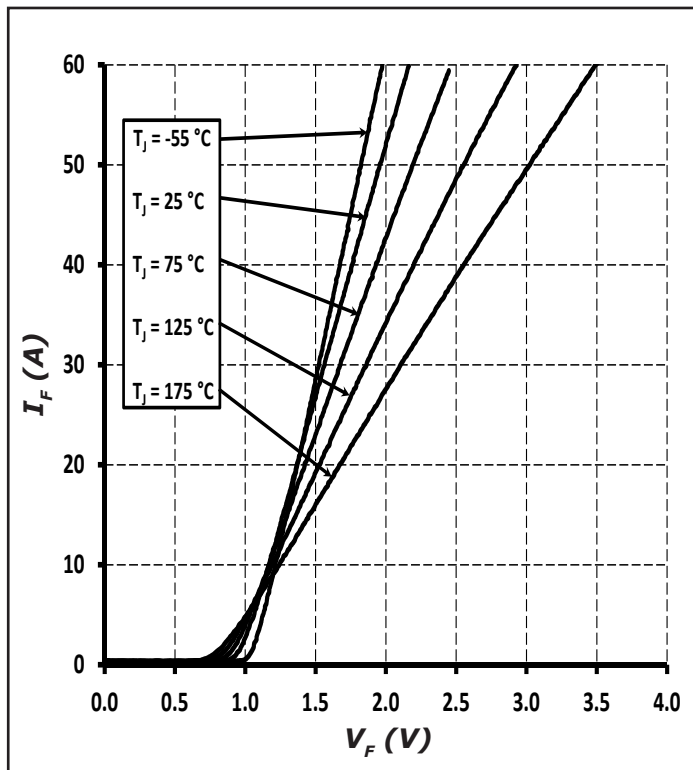


Figure 1. Forward Characteristics

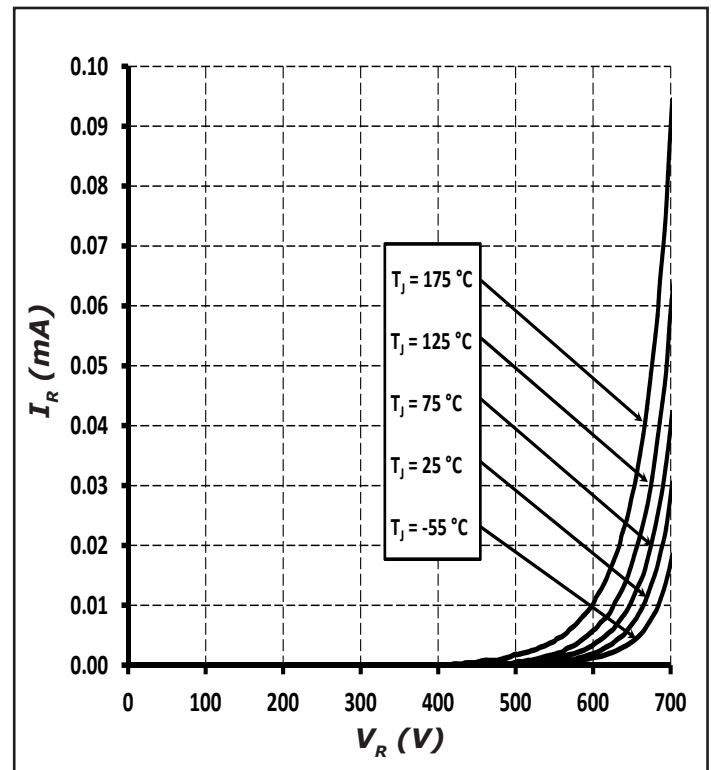


Figure 2. Reverse Characteristics

Typical Performance

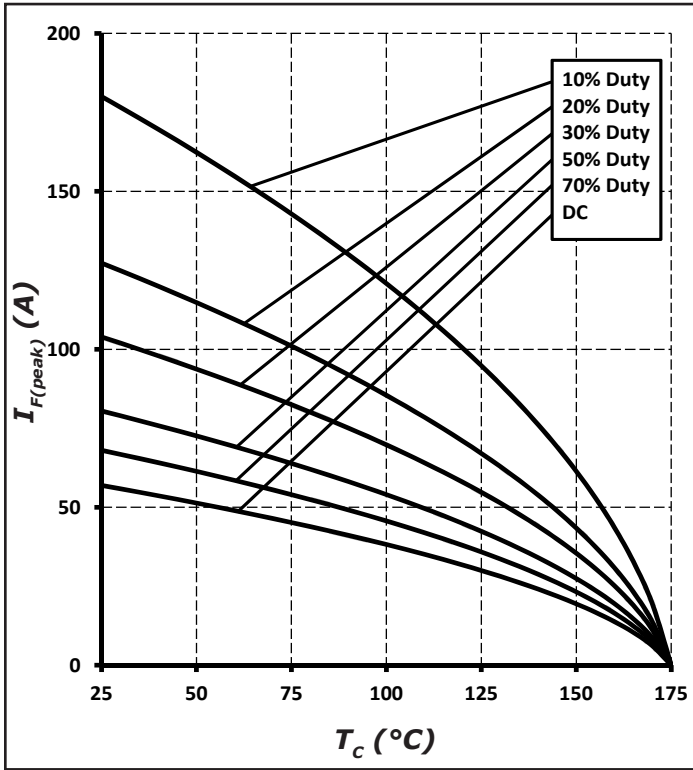


Figure 3. Current Derating

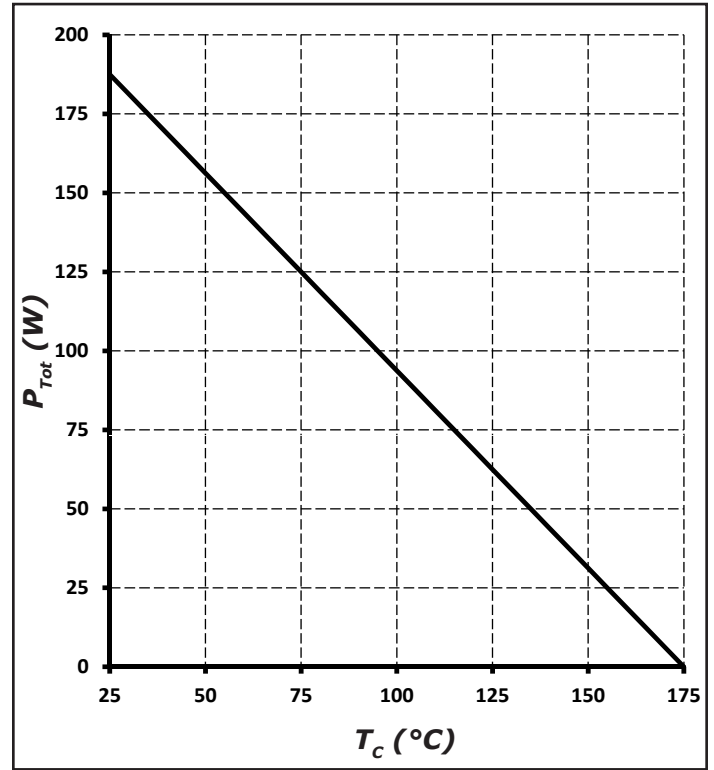


Figure 4. Power Derating

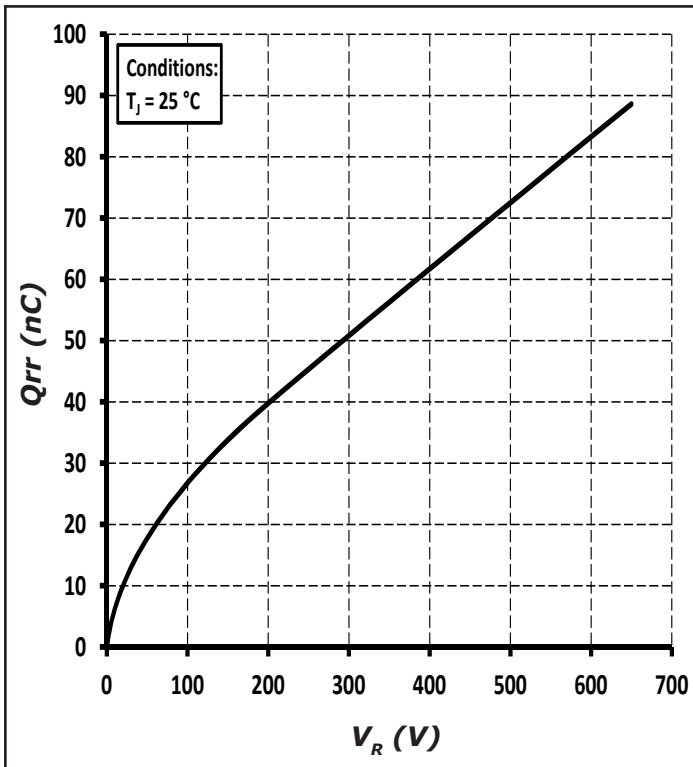


Figure 5. Recovery Charge vs. Reverse Voltage

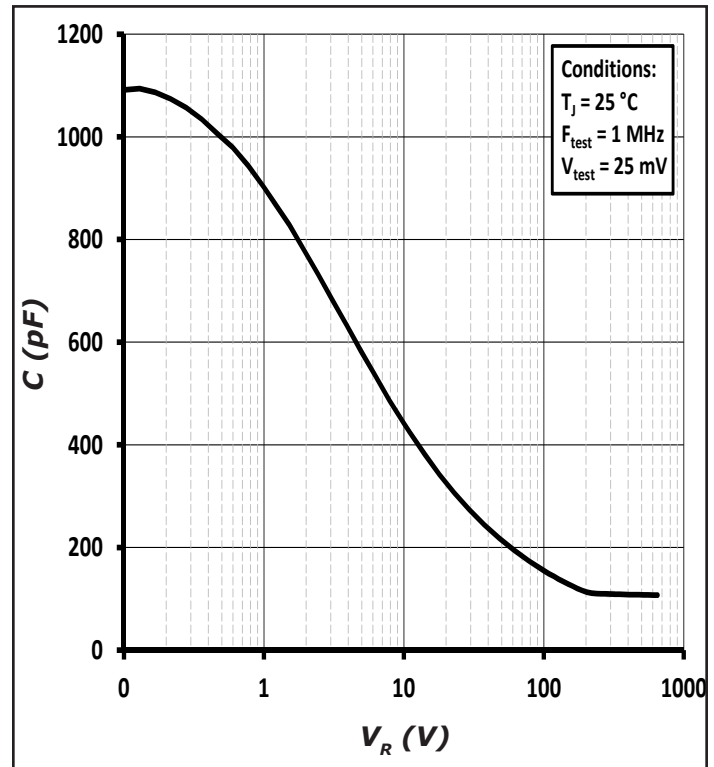


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

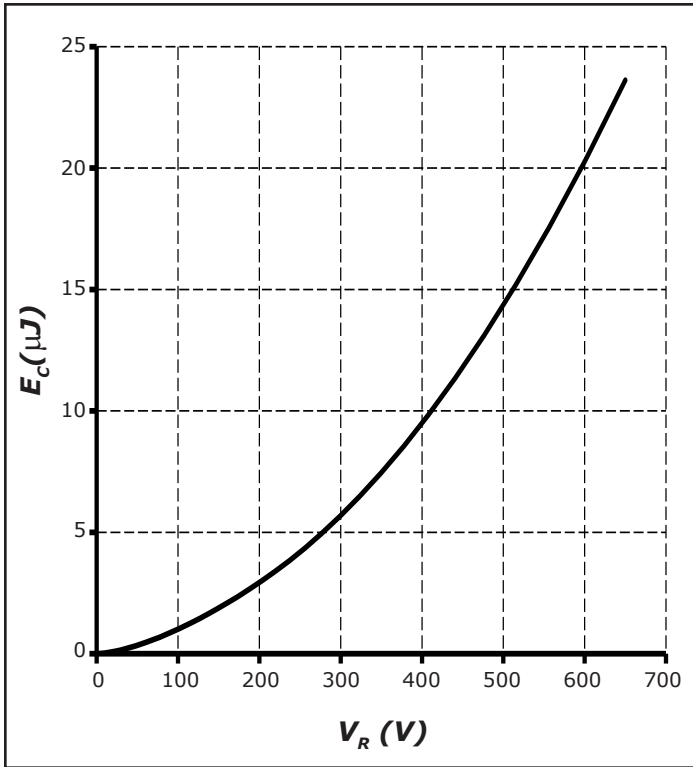


Figure 7. Typical Capacitance Stored Energy

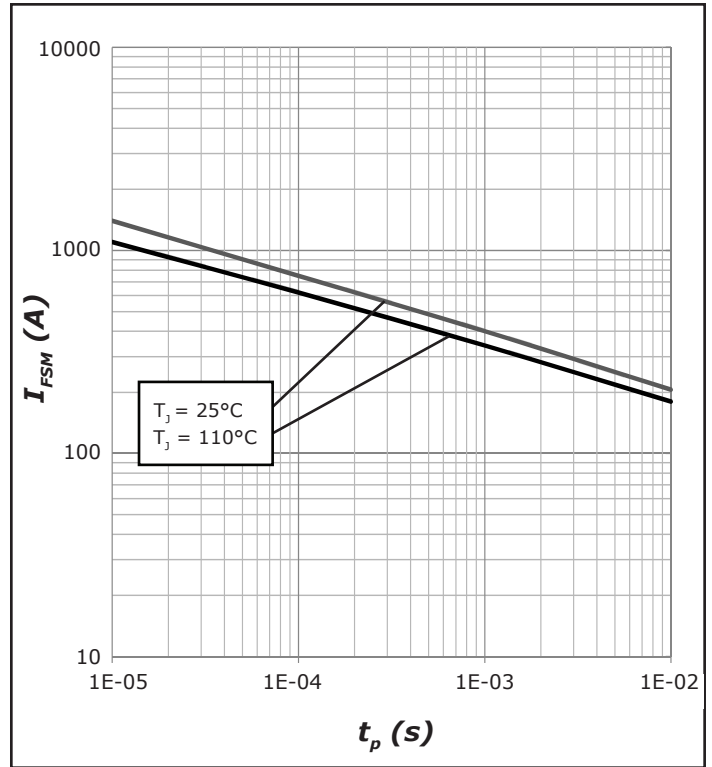


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

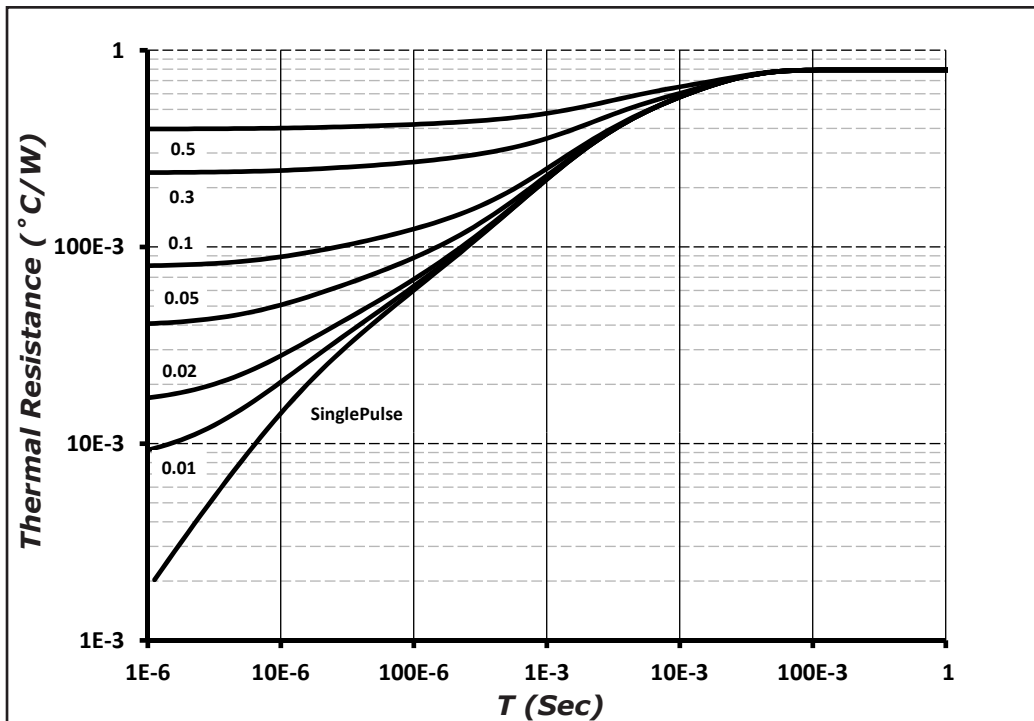
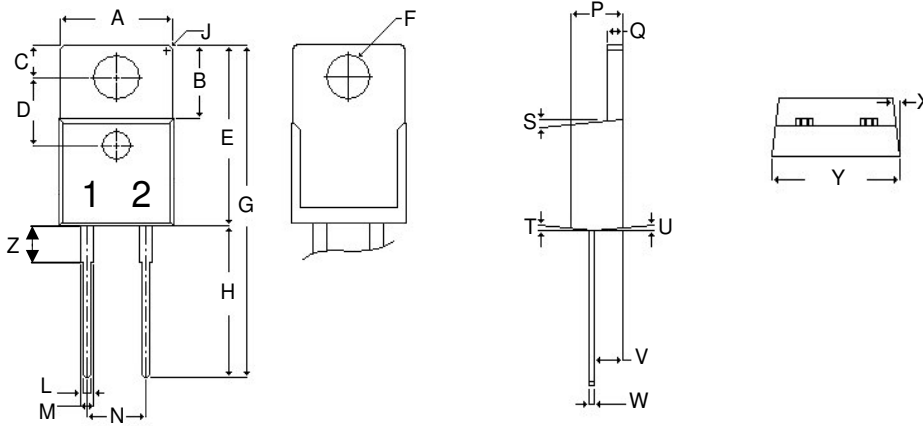


Figure 9. Transient Thermal Impedance

Package Dimensions

Package TO-220-2

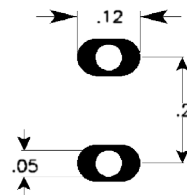


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.381	.410	9.677	10.414
B	.235	.255	5.969	6.477
C	.100	.120	2.540	3.048
D	.223	.337	5.664	8.560
E	.590	.615	14.986	15.621
F	.143	.153	3.632	3.886
G	1.105	1.147	28.067	29.134
H	.500	.550	12.700	13.970
J	R 0.197		R 0.197	
L	.025	.036	.635	.914
M	.045	.055	1.143	1.397
N	.195	.205	4.953	5.207
P	.165	.185	4.191	4.699
Q	.048	.054	1.219	1.372
S	3°	6°	3°	6°
T	3°	6°	3°	6°
U	3°	6°	3°	6°
V	.094	.110	2.388	2.794
W	.014	.025	.356	.635
X	3°	5.5°	3°	5.5°
Y	.385	.410	9.779	10.414
Z	.130	.150	3.302	3.810

NOTE:

1. Dimension L, M, W apply for Solder Dip Finish

Recommended Solder Pad Layout



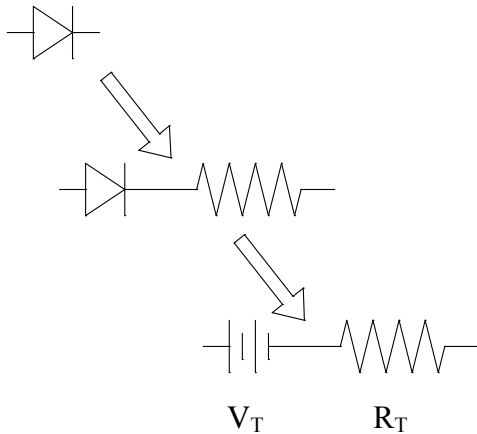
TO-220-2

Part Number	Package	Marking
CVFD20065A	TO-220-2	CVFD20065

Note: Recommended soldering profiles can be found in the applications note here: http://www.cree.com/power_app_notes/soldering



Diode Model



$$V_{fT} = V_T + I_f * R_T$$

$$V_T = 1.0081 + (T_j * -1.6 * 10^{-3})$$

$$R_T = 0.0146 + (T_j * 1.7 * 10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Notes

- **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

- **REACH Compliance**

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: <http://www.cree.com/diodes>
- C3D Spice models: http://response.cree.com/Request_Diode_model
- SiC MOSFET and diode reference designs: http://response.cree.com/SiC_RefDesigns



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.